

DMTH8012LPSW

80V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8 (SWP) (Type Q)

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _C = +25°C	
80V	$17m\Omega @ V_{GS} = 10V$	53.7A	
	$23.5 \text{m}\Omega$ @ $V_{GS} = 4.5 \text{V}$	44.3A	

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

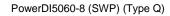
- Synchronous Rectifier
- Backlighting
- Power Management Functions
- DC-DC Converters

Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Additional Tin-plated on Sidewall Pads for Optical Solder Inspection
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

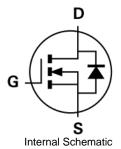
Mechanical Data

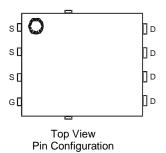
- Case: PowerDI[®]5060-8 (SWP) (Type Q)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.097 grams (Approximate)





Top View Bottom View





Ordering Information (Note 4)

Τ			
	Part Number	Case	Packaging
	DMTH8012LPSW-13	PowerDI5060-8 (SWP) (Type Q)	2,500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



Oll = Manufacturer's Marking
TH8012LSW = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 17 = 2017)
WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	80	V	
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 5)	$T_A = +25^{\circ}C$ $T_A = +100^{\circ}C$	I _D	10.3 7.3	А
Continuous Drain Current, $V_{GS} = 10V$ (Note 6) $ T_C = +25^{\circ}C $ $ T_C = +100^{\circ}C $		I _D	53.7 38	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	80	Α	
Maximum Continuous Body Diode Forward Current (Note	Is	69	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cy	I _{SM}	80	Α	
Avalanche Current, L=0.1mH	I _{AS}	11.6	Α	
Avalanche Energy, L=0.1mH	E _{AS}	6.7	mJ	

Thermal Characteristics

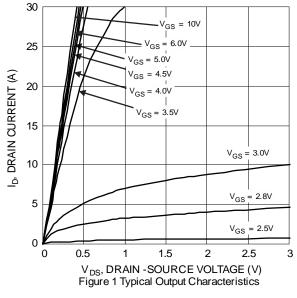
Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25$ °C	P_{D}	3.1	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{ heta JA}$	49	°C/W
Total Power Dissipation (Note 6)	T _C = +25°C	P_D	83.3	W
Thermal Resistance, Junction to Case (Note 6)		$R_{ heta JC}$	1.8	°C/W
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +175	°C

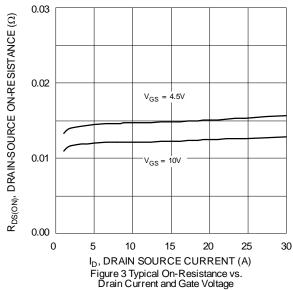
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

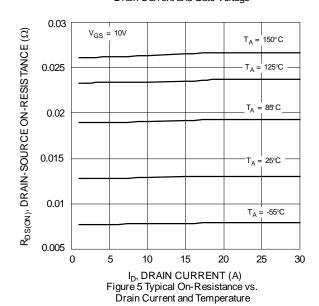
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	80	-	-	٧	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1	μΑ	$V_{DS} = 64V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1	-	3	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	Pagain	-	14	17	mΩ	$V_{GS} = 10V, I_D = 12A$	
Static Drain-Source Off-Resistance	R _{DS(ON)}	-	16.5	23.5		$V_{GS} = 4.5V, I_D = 6A$	
Diode Forward Voltage	V_{SD}	-	0.9	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	-	1949	-		$V_{DS} = 40V$, $V_{GS} = 0V$, $f = 1MHz$	
Output Capacitance	Coss	-	177	-	pF		
Reverse Transfer Capacitance	C _{rss}	-	10	-			
Gate Resistance	Rg	-	0.7	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	-	15	-			
Total Gate Charge (V _{GS} = 10V)	Qg	-	34	-	nC	V _{DS} = 40V, I _D = 12A	
Gate-Source Charge	Qgs	-	6	-	IIC		
Gate-Drain Charge	Q_{gd}	-	4.5	-			
Turn-On Delay Time	t _{D(ON)}	-	4.9	-		$V_{DD} = 40V, V_{GS} = 10V,$ $I_{D} = 12A, R_{g} = 1.6\Omega$	
Turn-On Rise Time	t _R	-	3.8	-	ns		
Turn-Off Delay Time	t _{D(OFF)}	-	16.5	-			
Turn-Off Fall Time	t _F	-	3.5	-			
Body Diode Reverse Recovery Time	t _{RR}	-	30.2	-	ns	I_ 12A di/dt 100A/va	
Body Diode Reverse Recovery Charge	Q _{RR}	-	34.6	-	nC	I _F = 12A, di/dt = 100A/μs	

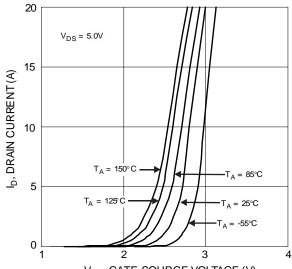
 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 Thermal resistance from junction to soldering point (on the exposed drain pad).
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing. Notes:



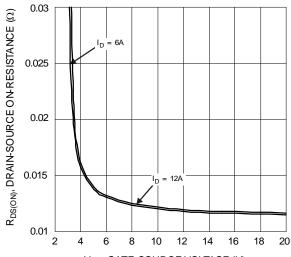




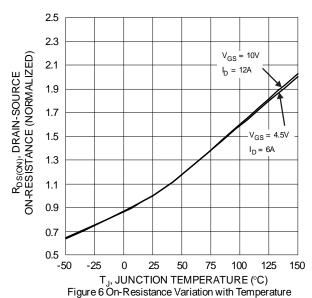




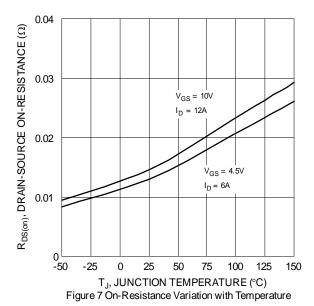
 $\rm V_{GS}$ GATE-SOURCE VOLTAGE (V) Figure 2 Typical Transfer Characteristics

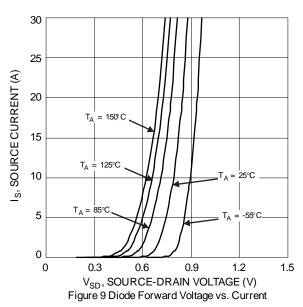


V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage









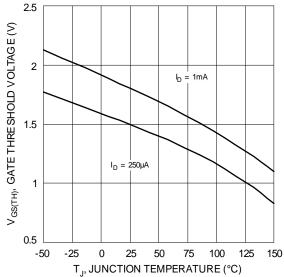
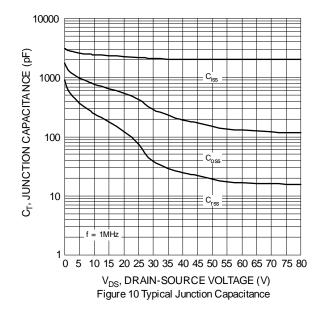
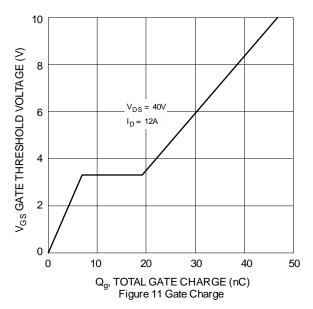
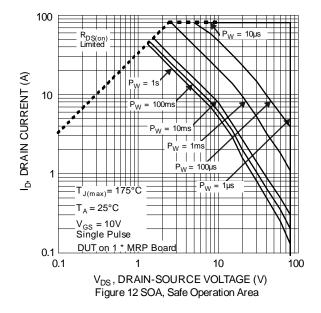


Figure 8 Gate Threshold Variation vs. Junction Temperature









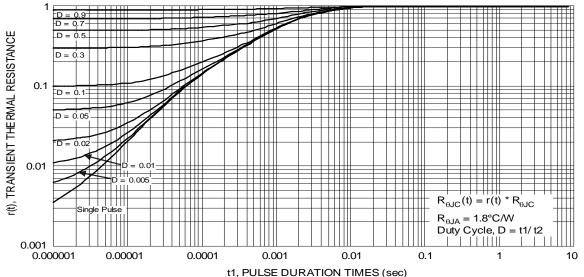


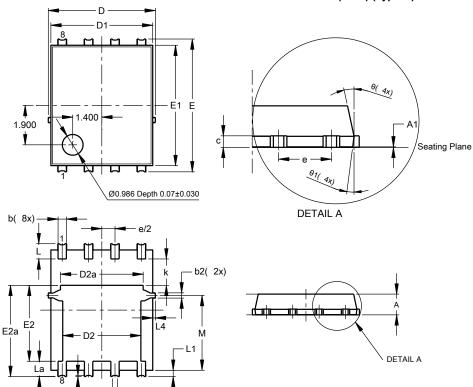
Figure 13 Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (SWP) (Type Q)

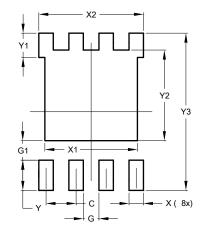


PowerDI5060-8 (SWP) (Type Q)					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0	0.05	-		
b	0.30	0.50	0.41		
b2	0.20	0.35	0.25		
b4	().25REF	-		
С	0.230	0.330	0.277		
D	5	.15 BS0)		
D1	4.70	4.70 5.10			
D2	3.56	3.96	3.76		
D2a	3.78	4.18	3.98		
E	6.40 BSC				
E1	5.60	6.00	5.80		
E2	3.46	3.86	3.66		
E2a	4.195	4.595	4.395		
е	1.27BSC				
k	1.05				
L	0.635	0.835	0.735		
La	0.635	0.835	0.735		
L1	0.200	0.400	0.300		
L1a	0.050REF				
L4	0.025	0.225	0.125		
M	3.205	4.005	3.605		
θ	10° 12°		11°		
θ1	6° 8° 7°		7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (SWP) (Type Q)



Dimensions	Value			
פווטופווסוטווס	(in mm)			
C	1.270			
G	0.660			
G1	0.820			
Х	0.610			
X1	4.100			
X2	4.420			
Y	1.270			
Y1	1.020			
Y2	3.810			
Y3	6.610			



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2017, Diodes Incorporated

www.diodes.com

ПОСТАВКА ЭЛЕКТРОННЫХ КОМПОНЕНТОВ

многоканальный

Общество с ограниченной ответственностью «МосЧип» ИНН 7719860671 / КПП 771901001 Адрес: 105318, г.Москва, ул.Щербаковская д.3, офис 1107

Данный компонент на территории Российской Федерации Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

http://moschip.ru/get-element

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г. Москва, ул. Щербаковская д. 3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru moschip.ru_6 moschip.ru 4 moschip.ru 9